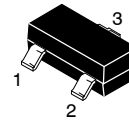


General Purpose Transistor

PNP Silicon

BCW68GL



SOT-23
CASE 318
STYLE 6

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

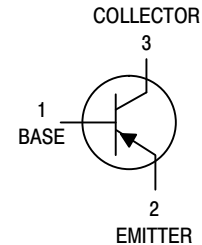
Symbol	Rating	Value	Unit
V_{CEO}	Collector-Emitter Voltage	-45	Vdc
V_{CBO}	Collector-Base Voltage	-60	Vdc
V_{EBO}	Emitter-Base Voltage	-5.0	Vdc
I_C	Collector Current - Continuous	-800	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

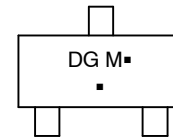
THERMAL CHARACTERISTICS

Symbol	Characteristic	Max	Unit
P_D	Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	225 1.8	mW mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	556	$^\circ\text{C}/\text{W}$
P_D	Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	300 2.4	mW mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	417	$^\circ\text{C}/\text{W}$
T_J, T_{stg}	Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.



MARKING DIAGRAM



DG = Specific Device Code
M = Date Code*
■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BCW68GLT1G, NSVBCW68GLT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BCW68GLT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BCW68GL

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristic	Min	Typ	Max	Unit
--------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C = -10\text{ mAdc}$, $I_B = 0$)	-45	-	-	Vdc
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ($I_C = -10\text{ }\mu\text{Adc}$, $V_{EB} = 0$)	-60	-	-	Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_E = -10\text{ }\mu\text{Adc}$, $I_C = 0$)	-5.0	-	-	Vdc
I_{CES}	Collector Cutoff Current ($V_{CE} = -45\text{ Vdc}$, $I_E = 0$) ($V_{CE} = -45\text{ Vdc}$, $I_B = 0$, $T_A = 150^\circ\text{C}$)	-	-	-20 -10	nAdc μAdc
I_{EBO}	Emitter Cutoff Current ($V_{EB} = -4.0\text{ Vdc}$, $I_C = 0$)	-	-	-20	nAdc

ON CHARACTERISTICS

h_{FE}	DC Current Gain ($I_C = -10\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -100\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -300\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$)	120 160 60	- - -	400 - -	-
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C = -500\text{ mAdc}$, $I_B = -50\text{ mAdc}$)	-	-	-0.7	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ($I_C = -500\text{ mAdc}$, $I_B = -50\text{ mAdc}$)	-	-	-2.0	Vdc

SMALL-SIGNAL CHARACTERISTICS

f_T	Current-Gain – Bandwidth Product ($I_C = -20\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$, $f = 100\text{ MHz}$)	100	-	-	MHz
C_{obo}	Output Capacitance ($V_{CB} = -10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	-	-	18	pF
C_{ibo}	Input Capacitance ($V_{EB} = -0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	-	-	105	pF
N_F	Noise Figure ($I_C = -0.2\text{ mAdc}$, $V_{CE} = -5.0\text{ Vdc}$, $R_S = 1.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$)	-	-	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

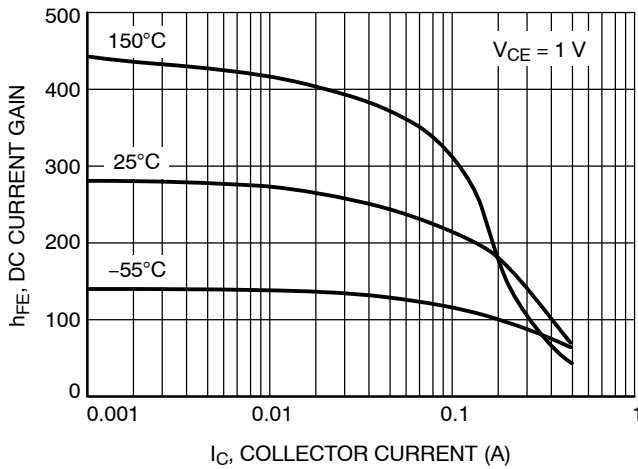


Figure 1. DC Current Gain vs. Collector Current

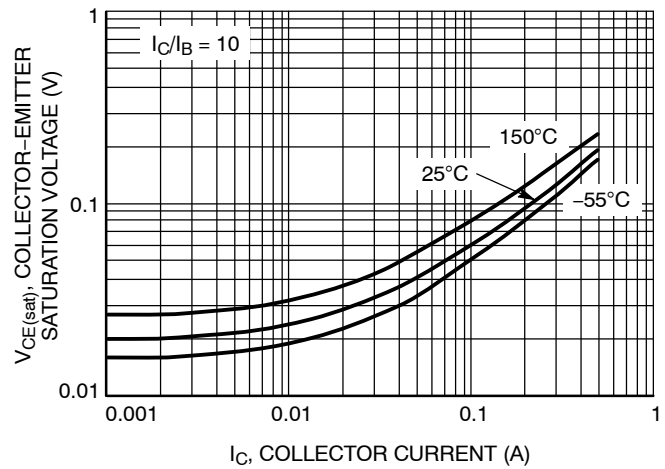


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

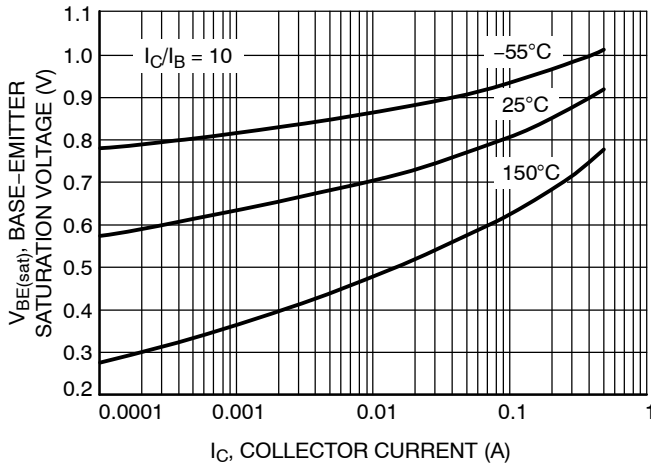


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

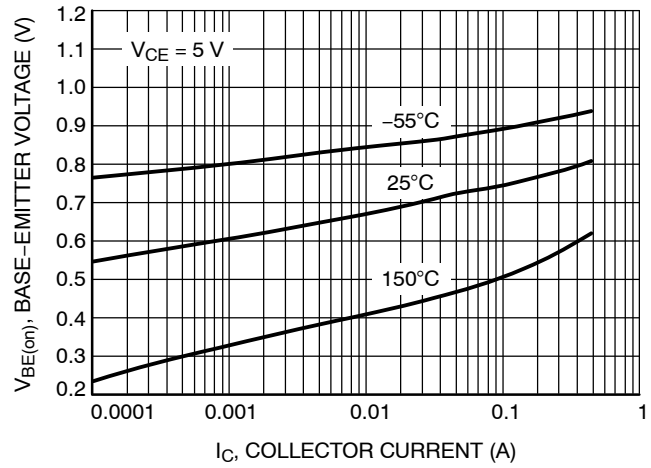


Figure 4. Base Emitter Voltage vs. Collector Current

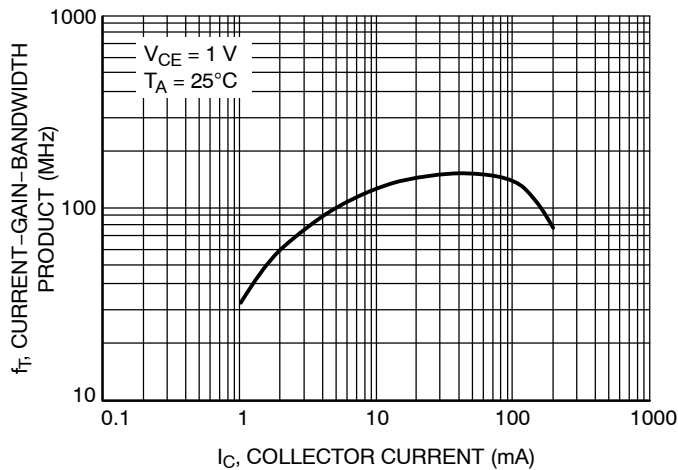


Figure 5. Current Gain Bandwidth Product vs. Collector Current

BCW68GL

TYPICAL CHARACTERISTICS (continued)

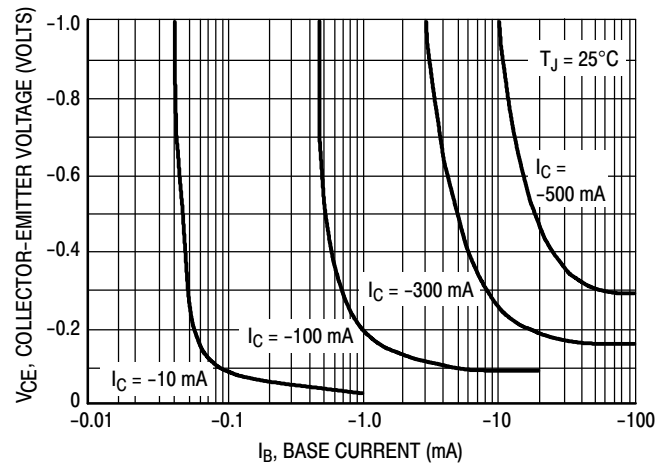


Figure 6. Saturation Region

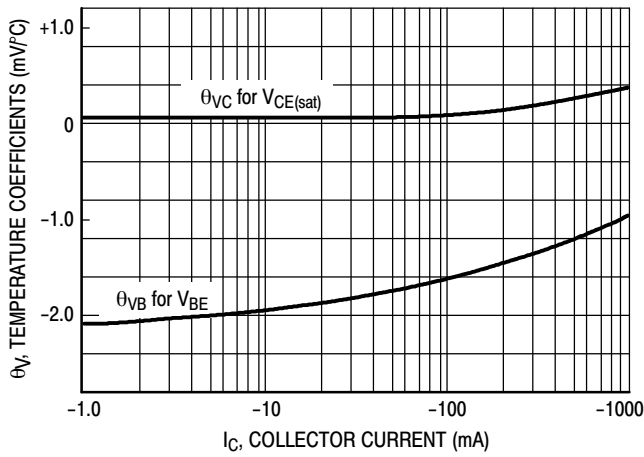


Figure 7. Temperature Coefficients

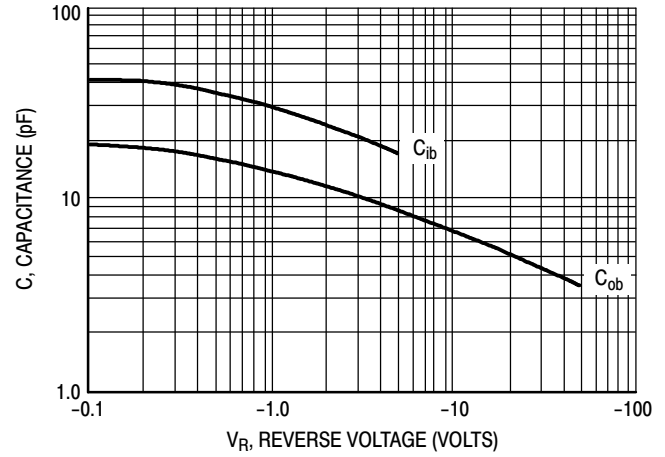
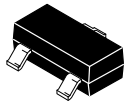


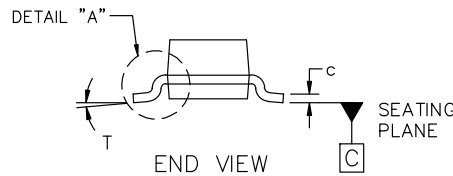
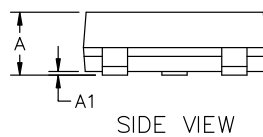
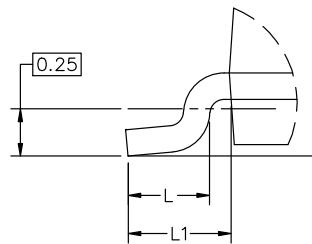
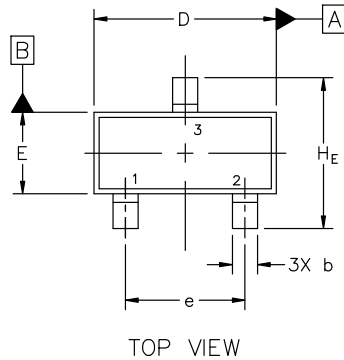
Figure 8. Capacitances



SCALE 4:1

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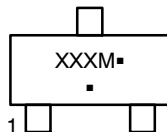


MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

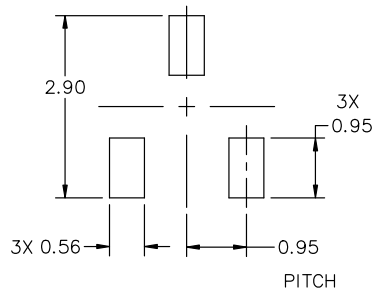
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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ISSUE AU

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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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